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December 2013

# **FDPF390N15A**

# N-Channel PowerTrench® MOSFET

#### 150 V, 15 A, 40 mΩ

#### **Features**

- $R_{DS(on)}$  = 31 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 15 A
- · Fast Switching Speed
- Low Gate Charge, Q<sub>G</sub> = 14.3 nC (Typ.)
- High Performance Trench Technology for Extremely Low  $R_{\mbox{\footnotesize{DS(on)}}}$
- · High Power and Current Handling Capability
- · RoHS Compliant

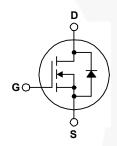
#### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintain-ing superior switching performance.

#### **Applications**

- · Consumer Appliances
- LED TV
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Motor Solar Inverter





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDPF390N15A	Unit	
V <sub>DSS</sub>	Drain to Source Voltage			150	V	
V <sub>GSS</sub>	Gate to Source Voltage			±20	V	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C,Silicon Limited	d)	15	А	
	Dialii Current	- Continuous (T <sub>C</sub> = 100°C,Silicon Limite	ed)	10	_ ^	
I <sub>DM</sub>	Drain Current	- Pulsed (No	ote 1)	60	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Er	nergy (Ne	ote 2)	78	mJ	
dv/dt	Peak Diode Recovery dv/dt	(No	ote 3)	6.0	V/ns	
D	Device Dissipation	$(T_C = 25^{\circ}C)$		22	W	
$P_{D}$	Power Dissipation	- Derate above 25°C		0.18	W/°C	
$T_J$ , $T_{STG}$	Operating and Storage Temperature Range			-55 to +175	οС	
$T_L$	Maximum Lead Temperatur	e for Soldering, 1/8" from Case for 5 Seconds	-	300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FDPF390N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	5.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	- 0/00

## **Package Marking and Ordering Information**

	Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
F	FDPF390N15A	FDPF390N15A	TO-220F	Tube	N/A	N/A	50 units

### Electrical Characteristics $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$	-	0.1	-	V/ºC
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V	-	-	1	μА
D00	3 · · · · · · · · · · · · · · · · · · ·	$V_{DS} = 120 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	500	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	٧
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 15 \text{A}$	-	31	40	mΩ
9FS	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	-	32	-	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 75 V V 0 V	-	965	1285	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$ - f = 1 MHz	_	96	130	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12	-	5.8	-	pF
C <sub>oss(er)</sub>	Energy Related Output Capacitance	V <sub>DS</sub> = 75 V,V <sub>GS</sub> = 0 V		169	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V		-	14.3	18.6	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DS} = 75 \text{ V}, I_{D} = 27 \text{ A}$		5.0	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	V <sub>GS</sub> = 10 V	-	2.0	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4)	-	3.5	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1.4	-	Ω

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	14	38	ns
t <sub>r</sub>		$V_{DD} = 75 \text{ V}, I_D = 27 \text{ A}$	-	10	30	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	/ -	20	50	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	5	20	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode	Maximum Continuous Drain to Source Diode Forward Current			15	Α
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current			-	64	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	Drain to Source Diode Forward Voltage V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 15 A		-	1.25	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 27 A		63	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{GS} = 0 \text{ V, } I_{SD} = 27 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	131	_	nC

- **Notes:**1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. Starting  $T_J = 25$ °C, L = 3 mH,  $I_{SD} = 7.2$  A
- 3.  $I_{SD} \le 15$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J = 25^{\circ}C$
- 4. Essentially independent of operating temperature typical characteristics.

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

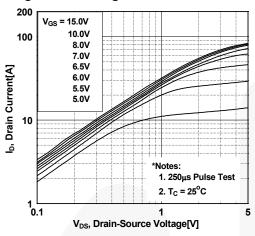


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

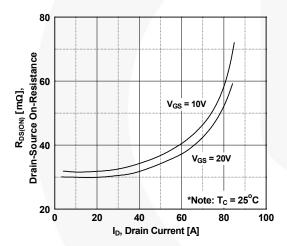
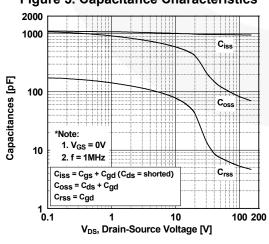


Figure 5. Capacitance Characteristics



**Figure 2. Transfer Characteristics** 

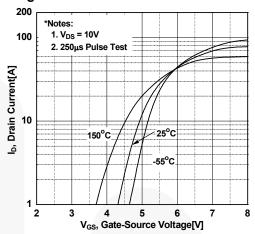


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

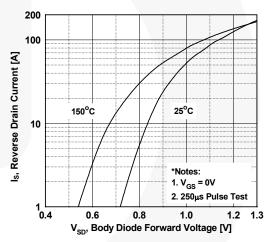
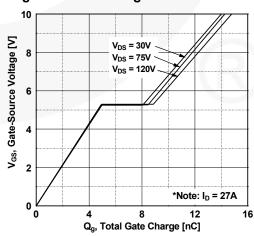


Figure 6. Gate Charge Characteristics



#### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

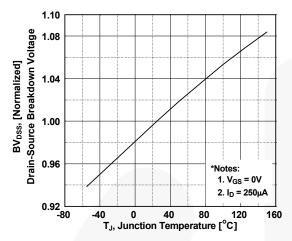


Figure 9. Maximum Safe Operating Area

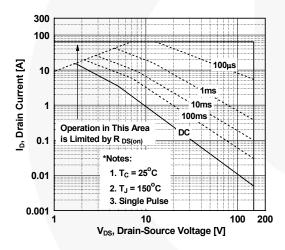


Figure 11. Eoss vs. Drain to Source Volatage

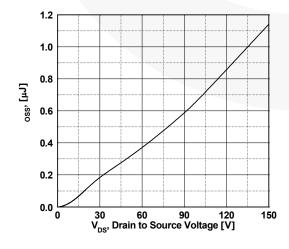


Figure 8. On-Resistance Variation vs. Temperature

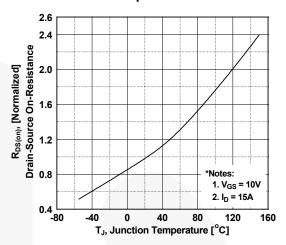


Figure 10. Maximum Drain Current vs. Case Temperature

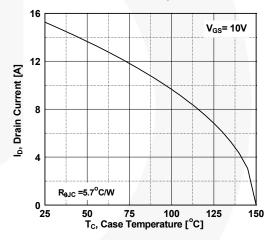
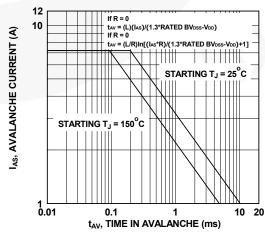
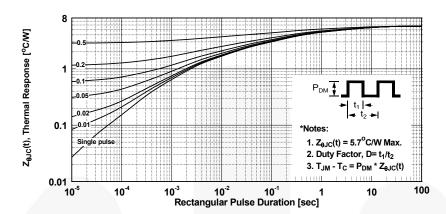


Figure 12. Unclamped Inductive Switching Capability



# **Typical Performance Characteristics** (Continued)

Figure 13. Transient Thermal Response Curve



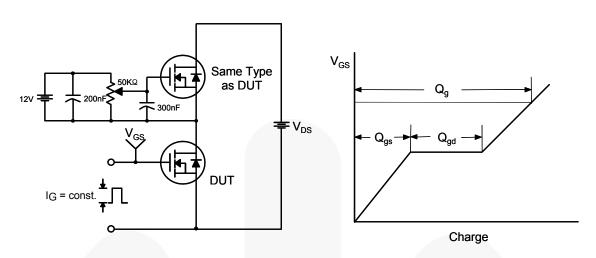


Figure 14. Gate Charge Test Circuit & Waveform

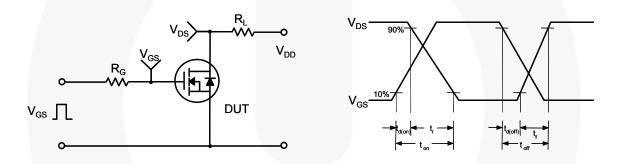


Figure 15. Resistive Switching Test Circuit & Waveforms

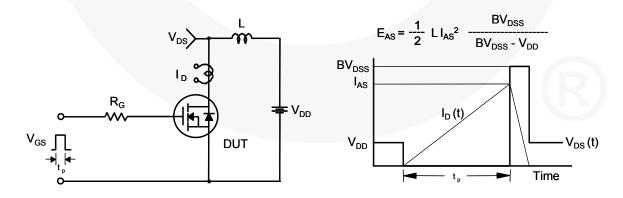


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

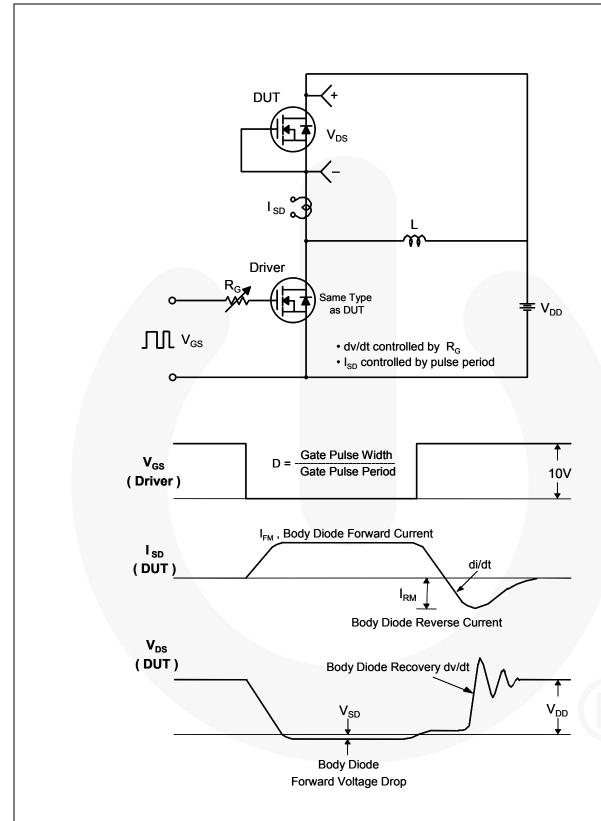
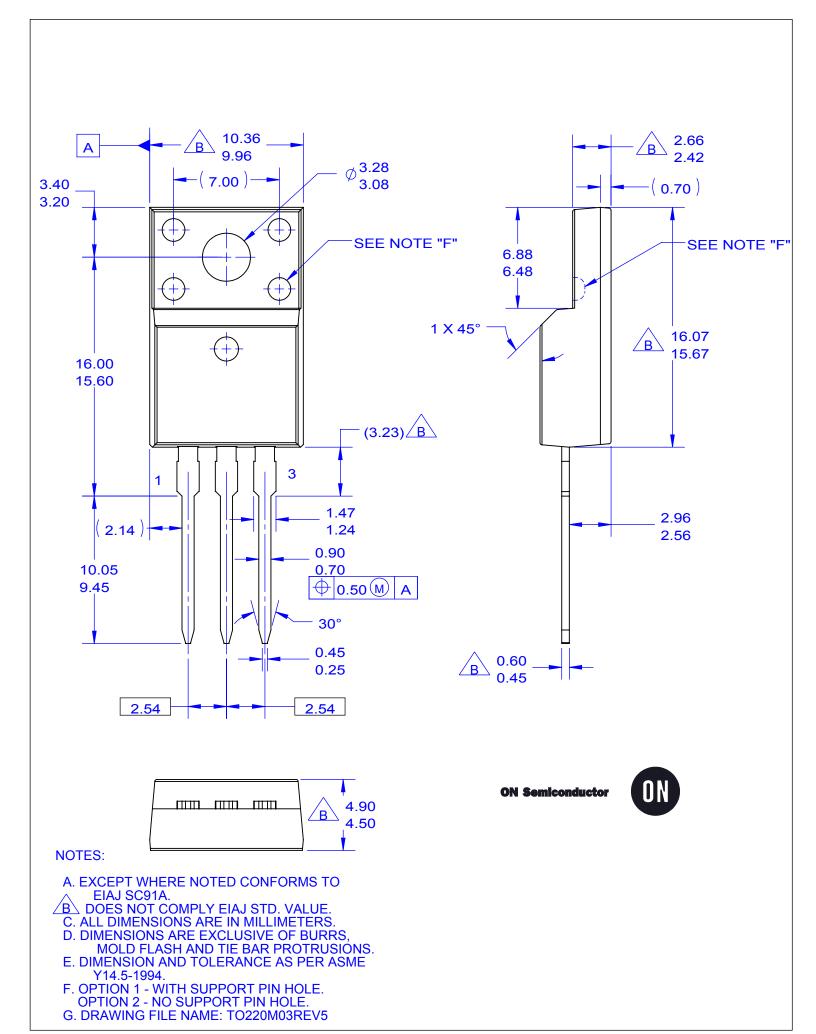


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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